Power MOSFET 20V, 22mΩ, 8A, Single N-Channel



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R_{DS}(on) Max

22mΩ@ 4.5V

ID Max

VDSS

Features

- Low On-Resistance

28mΩ@ 2.5V 20V 8A • 1.2V Drive 39mΩ@ 1.8V • ESD Diode-Protected Gate 124mΩ@ 1.2V • Pb-Free, Halogen Free and RoHS Compliance

Specifications

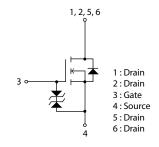
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	20	٧
Gate to Source Voltage	V _{GSS}	±9	٧
Drain Current (DC)	ID	8	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	32	А
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

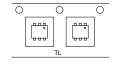
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient			
When mounted on ceramic substrate	$R_{\theta JA}$	83.3	°C/W
(1200mm ² × 0.8mm)			

Electrical Connection N-Channel



Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

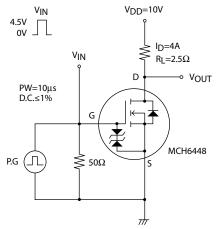
See detailed ordering and shipping information on page 5 of this data sheet.

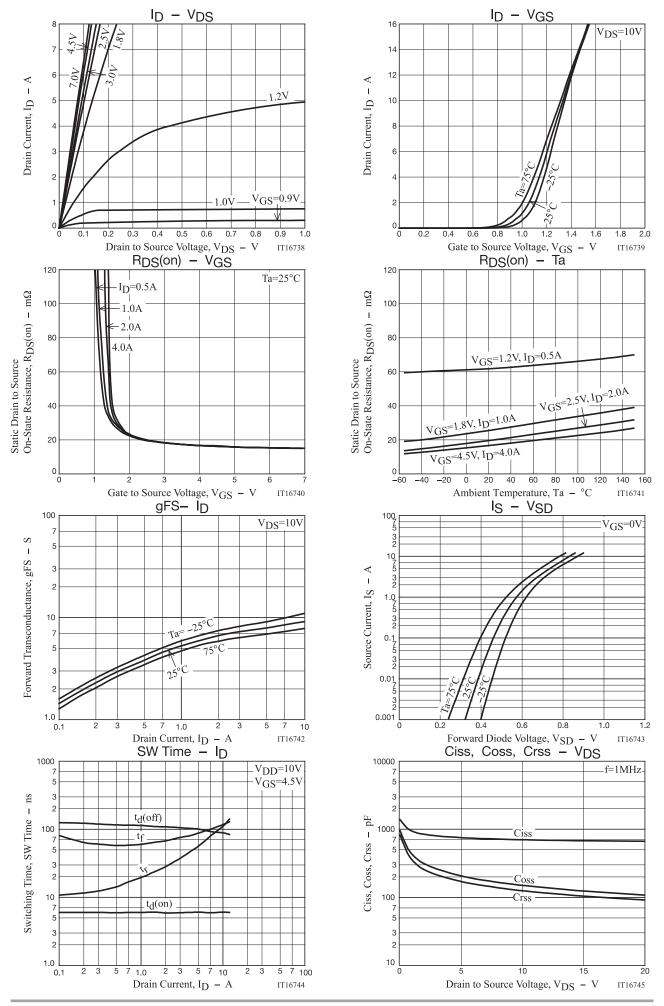
Electrical Characteristics at Ta = 25°C

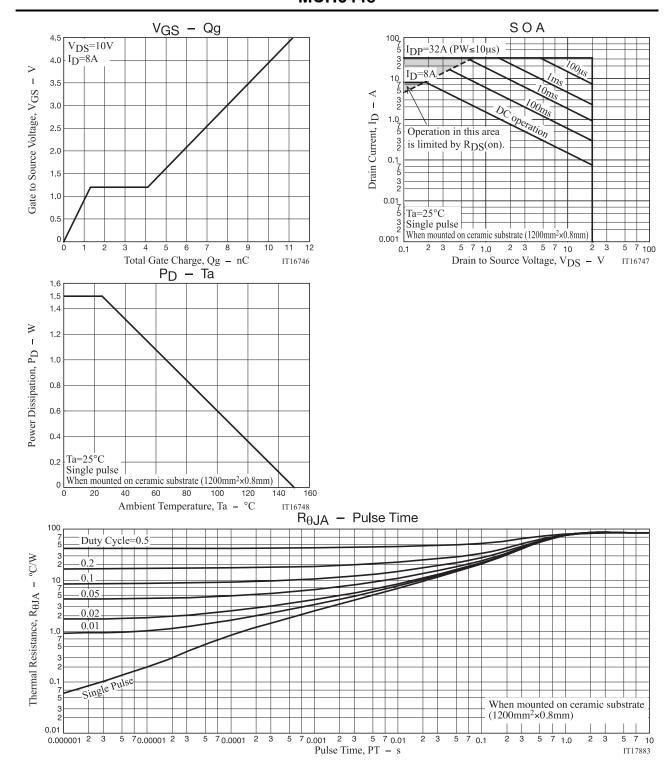
Desembles	O. made al	Conditions	Value		11-24	
Parameter	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±7.2V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	0.3		1.0	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =4A		7.7		S
	R _{DS} (on)1	I _D =4A, V _{GS} =4.5V		17	22	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =2A, V _{GS} =2.5V		20	28	mΩ
	R _{DS} (on)3	I _D =1A, V _{GS} =1.8V		26	39	mΩ
	R _{DS} (on)4	I _D =0.5A, V _{GS} =1.2V		62	124	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		705		pF
Output Capacitance	Coss			150		pF
Reverse Transfer Capacitance	Crss			125		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		6		ns
Rise Time	t _r			47		ns
Turn-OFF Delay Time	t _d (off)			103		ns
Fall Time	tf			81		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4.5V, I _D =8A		11.2		nC
Gate to Source Charge	Qgs			1.3		nC
Gate to Drain "Miller" Charge	Qgd]		2.8		nC
Forward Diode Voltage	V _{SD}	I _S =8A, V _{GS} =0V		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







Package Dimensions

MCH6448-TL-H / MCH6448-TL-W

MCPH6

CASE 419AS ISSUE O

unit: mm

1: Drain

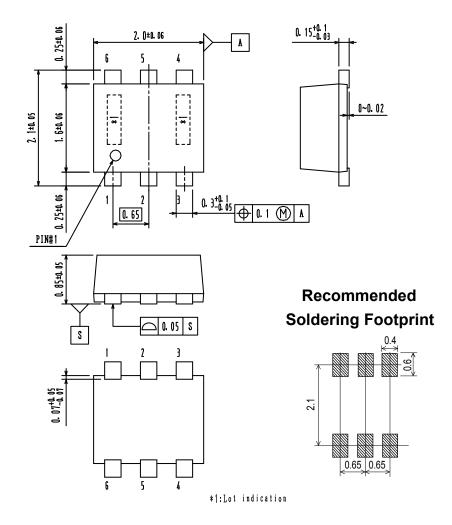
2: Drain

3: Gate

4: Source

5: Drain

6: Drain



ORDERING INFORMATION

Device	Package	Shipping	Note	
MCH6448-TL-H	MCPH6	3,000 pcs. / Tape & Reel	Pb-Free	
MCH6448-TL-W	SC-88FL,SC-70-6,SOT-363	3,000 pcs. / Tape & Reel	and Halogen Free	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6448 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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